Product data sheet

1. General description

Hyperfast power diode in a TO220-2L plastic package





2. Features and benefits

- Soft reverse recovery
- · Excellent avalanche energy robustness
- Low leakage current
- · Low thermal resistance
- · Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit		
Absolute maximum rating									
V_{RRM}	repetitive peak reverse voltage			650			V		
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 106$ °C; Fig. 1; Fig. 2; Fig. 3		30			А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; T_{mb} ≤ 106 °C; square-wave pulse		60			А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>		270		А			
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297		Α			
Symbol	Parameter	Conditions	Notes	s Min Typ Max		Max	Unit		
Static ch	aracteristics								
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.10	2.60	V		
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.45	1.90	V		
Dynamic characteristics									
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	20	24	ns		

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	5 🖯 7	к — Д— А
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathod		

6. Ordering information

Table 3. Ordering information

Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	name		method	quantity	version	issue date
BYC30M-650PS	TO220-2L	BYC30M-650PSQ	Tube	50	TO220d-2L	13-Oct-2022

7. Marking

Table 4. Marking codes

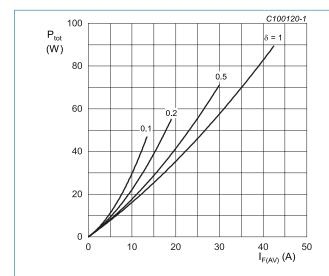
Type number	Marking codes
BYC30M-650PS	BYC30M 650PS

8. Limiting values

Table 5. Limiting values

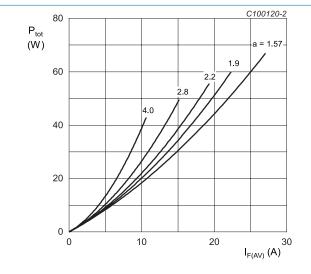
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 106 °C; Fig. 1; Fig. 2; Fig. 3		30	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 106 °C; square-wave pulse		60	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	А
T _{stg}	storage temperature			-65 to 175	°C
T _j	junction temperature			-65 to 175	°C



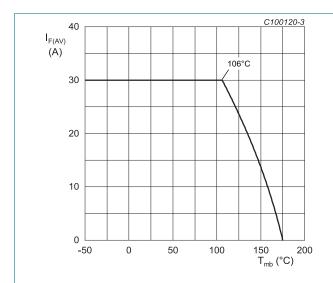
$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.465 \text{ V; } R_s = 0.0151 \text{ } \Omega \end{split}$$

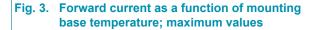
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.465 V; R_s = 0.0151 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





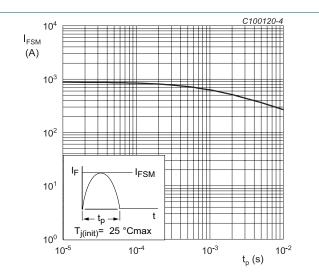


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	0.97	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

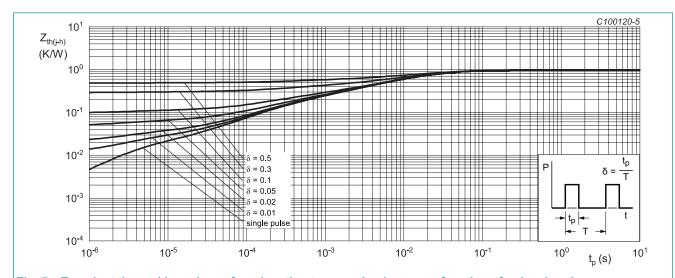
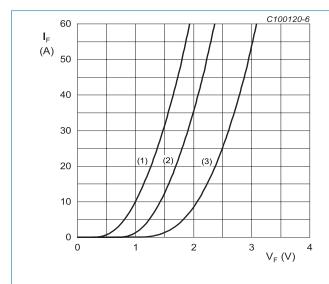


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	naracteristics						
V_{F}	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.10	2.60	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.45	1.90	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.43	30	μA
		V _R = 650 V; T _j = 150 °C		-	0.08	0.5	mA
Dynamic	characteristics						
Q _r	reverse charge	$I_F = 30 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 7		-	126	-	nC
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	505	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	20	24	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	67	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	105	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_J = 25 \text{ °C}$; Fig. 7		-	3.8	-	А
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	9.3	-	А
S _{factor}	softness factor	$I_F = 30 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 125 \text{ °C}$; Fig. 7		-	0.61	-	
E _{as}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		40	-	-	mJ



 V_o = 1.465 V; R_s = 0.0151 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values



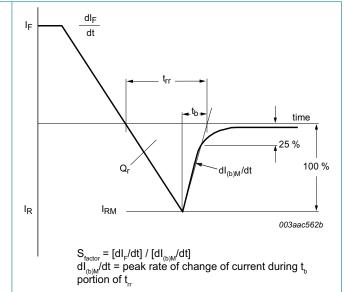


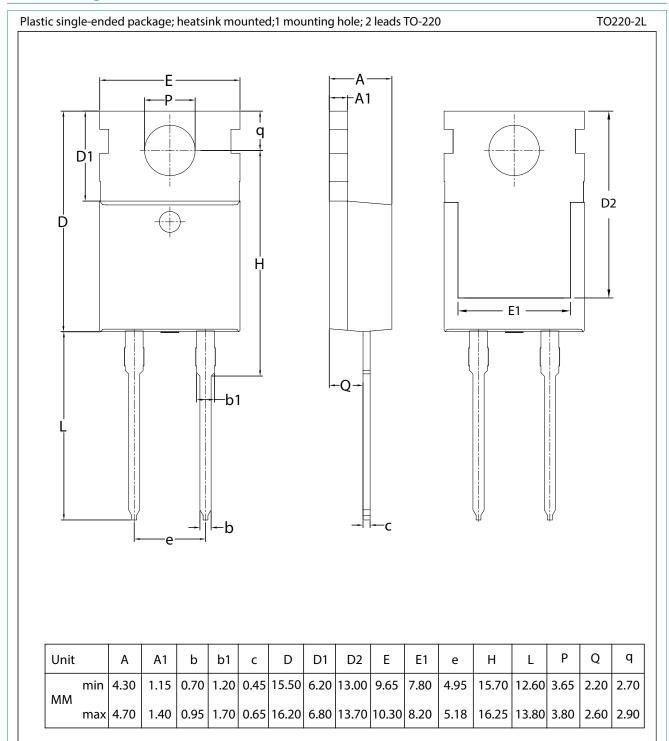
Fig. 7. Reverse recovery definitions; ramp recovery

BYC30M-650PS

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11. Package outline



Note:

1. All dimensions don't include mold flash and metal protrusion.

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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